

Title (en)

METHOD FOR MICROFABRICATING STRUCTURES USING SILICON-ON-INSULATOR MATERIAL

Title (de)

VERFAHREN ZUR MIKROHERSTELLUNG VON STRUKTUREN UNTER VERWENDUNG VON SILIZIUM-AUF-ISOLATOR-MATERIAL

Title (fr)

PROCEDE DE MICROUSINAGE DE STRUCTURES UTILISANT UN MATERIAU DE SILICIUM SUR ISOLANT

Publication

EP 1576650 A4 20110615 (EN)

Application

EP 03754388 A 20030815

Priority

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Abstract (en)

[origin: WO2004017371A2] The invention provides a general fabrication method for producing MicroElectroMechanical Systems (MEMS) and related devices using Silicon-On-Insulator (SOI) wafer. The method includes providing an SOI wafer that has (i) a handle layer, (ii) a dielectric layer, and (iii) a device layer, wherein a mesa etch has been made on the device layer of the SOI wafer, providing a substrate, wherein a pattern has been etched onto the substrate, bonding the SOI wafer and the substrate together, removing the handle layer of the SOI wafer, removing the dielectric layer of the SOI wafer, then performing a structural etch on the device layer of the SOI wafer to define the device.

IPC 8 full level

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Citation (search report)

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- [X] MOCHIDA Y ET AL: "A micromachined vibrating rate gyroscope with independent beams for the drive and detection modes", SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, vol. 80, no. 2, 1 March 2000 (2000-03-01), pages 170 - 178, XP004192104, ISSN: 0924-4247, DOI: 10.1016/S0924-4247(99)00263-0
- See references of WO 2004017371A2

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